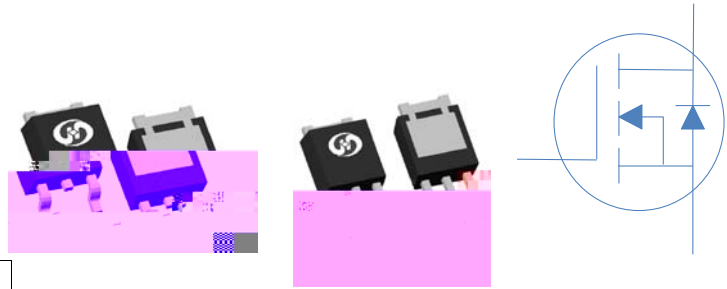


100V N-Ch Power MOSFET

DS(on), typ			Ω
DS(on), typ			Ω



	TO-251	
	TO-252	

=25 (unless otherwise specified)

		=25		
		=100		
Avalanche Energy, Single Pulse	E	=25		
Power Dissipation		=25		W
Operating and Storage Temperature				

Thermal Resistance Junction-Ambient	θ		M
Thermal Resistance Junction-Case	θ		M





Fig 1. Typical Output Characteristics

Figure 2. On-Resistance vs. Gate-Source Voltage

Figure 3. On-Resistance vs. Drain Current and Gate Voltage

Figure 4. Normalized On-Resistance vs. Junction Temperature

Figure 5. Typical Transfer Characteristics

Figure 6. Typical Source-Drain Diode Forward Voltage



Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

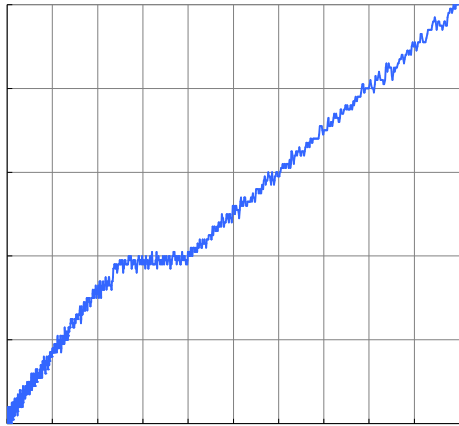


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case



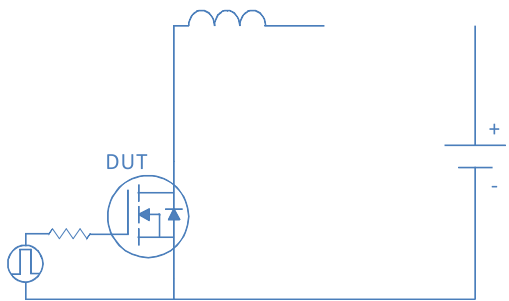
Inductive switching Test

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Gate Charge Test

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Uclamped Inductive Switching (UIS) Test

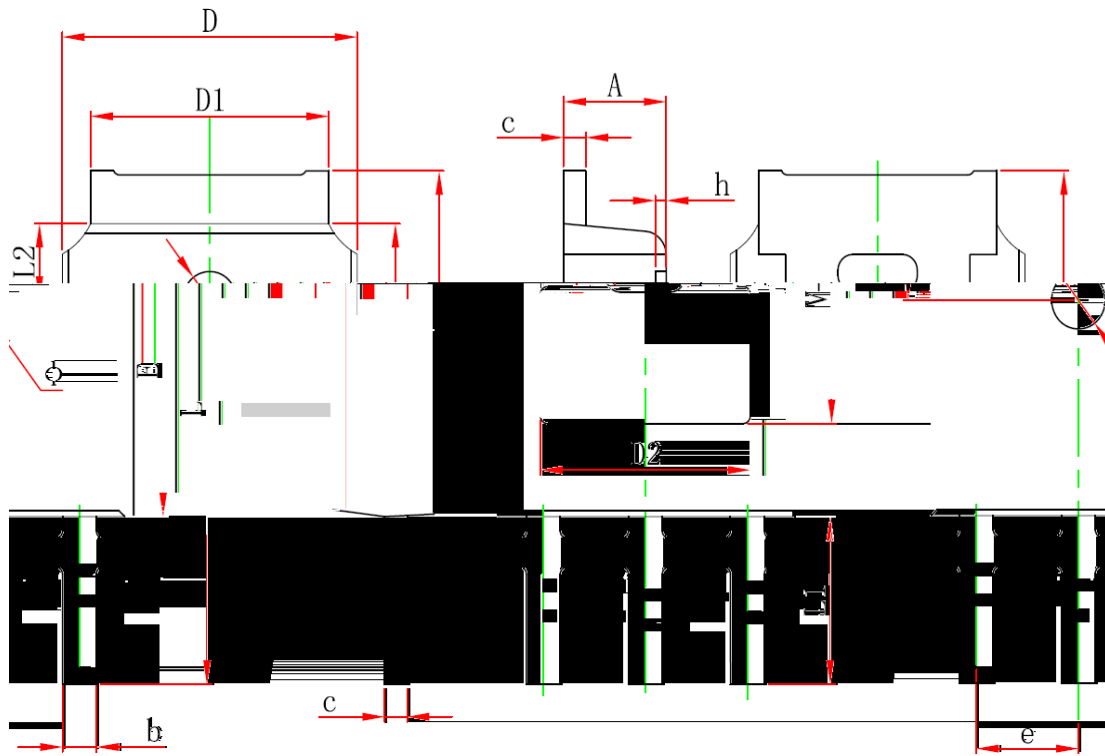


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Package Outline

TO-251, 3 leads



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN.	MAX.	MIN.	MAX.
0.094	A	2.200	2.400	0.087
0.034	b	0.660	0.860	0.026
0.023	c	0.460	0.580	0.018
0.256	D	6.500	6.700	
0.201	D1	5.100	5.460	
0.190 REF.	D2	4.830 REF.		
0.236	e	6.000	6.200	

